A B S T R A C T

The present invention provides a SOI wafer produced by an ion implantation delamination method wherein a width of a SOI island region in a terrace portion generated in an edge portion of the SOI wafer where a surface of a base wafer is exposed is narrower than 1 mm and a density of pit-shaped defects having a size of 0.19 μm or more existing in a surface of a SOI layer detected by a LPD inspection is 1 counts/cm^2 or less, and also provides a method for producing the SOI wafer. Thereby, there is provided a SOI wafer produced by an ion implantation delamination method wherein generation of SOI islands generated in delamination can be suppressed and a defect density of LPDs existing in a surface of the SOI wafer can be reduced, and a method for producing the same, so that device failure can be reduced.



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